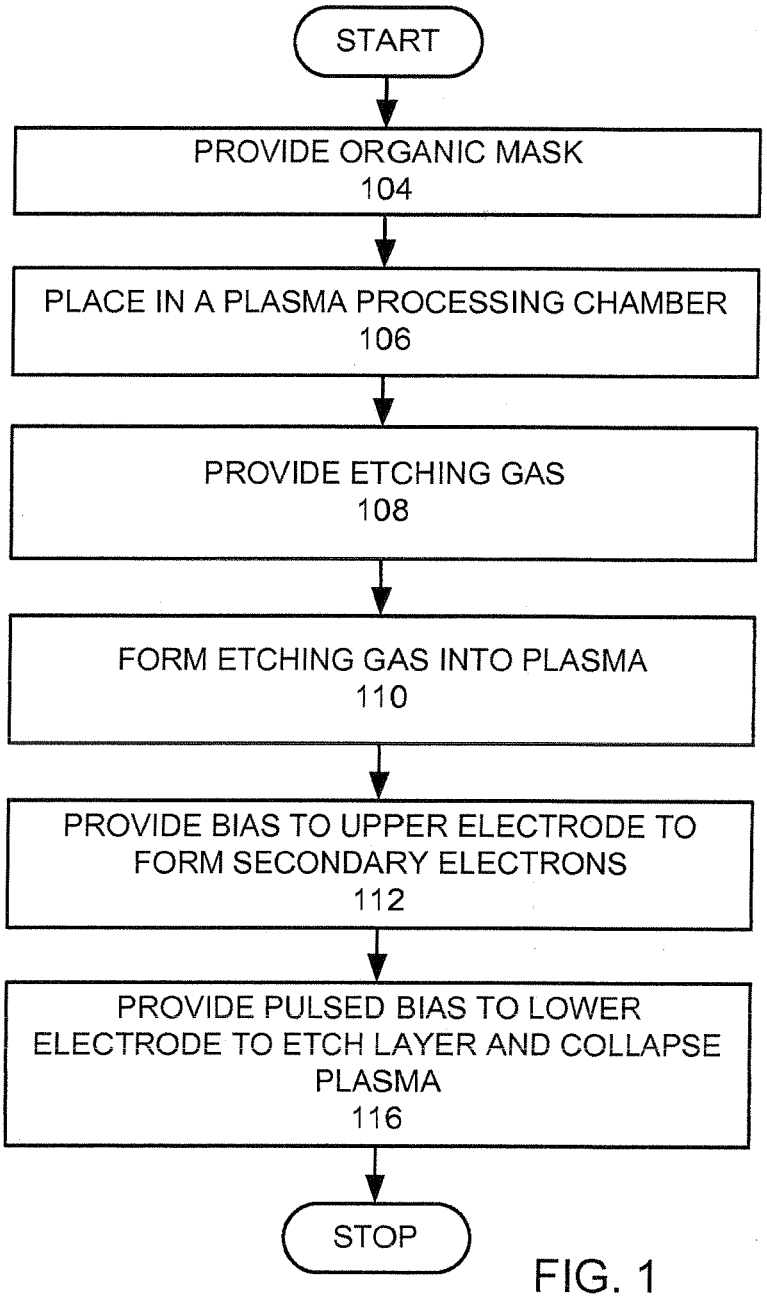

START
PROVIDE ORGANIC MASK
104
PLACE IN A PLASMA PROCESSING CHAMBER
106
PROVIDE ETCHING GAS
108
FORM ETCHING GAS INTO PLASMA
110
PROVIDE BIAS TO UPPER ELECTRODE TO FORM SECONDARY ELECTRONS
112
PROVIDE PULSED BIAS TO LOWER ELECTRODE TO ETCH LAYER AND COLLAPSE PLASMA
116
STOP

FIG. 1

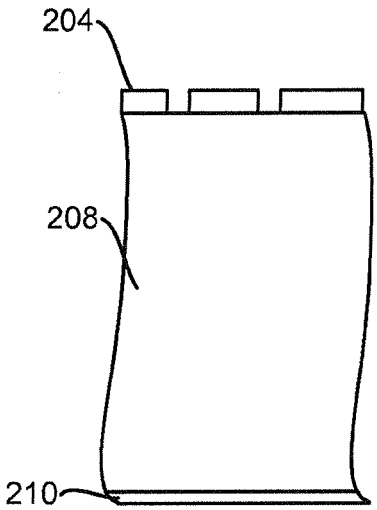


FIG. 2A

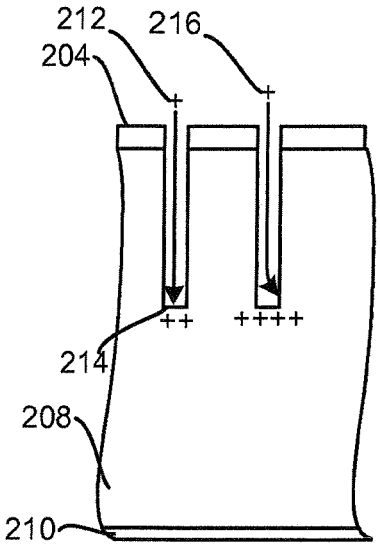


FIG. 2B

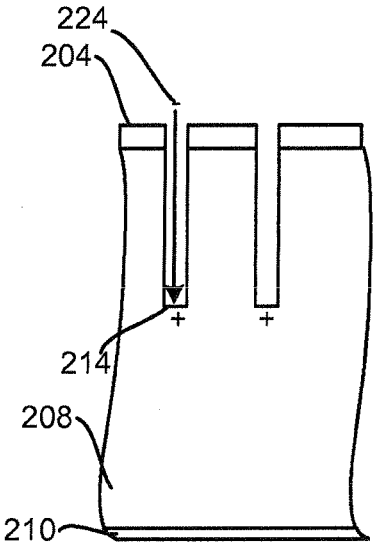


FIG. 2C

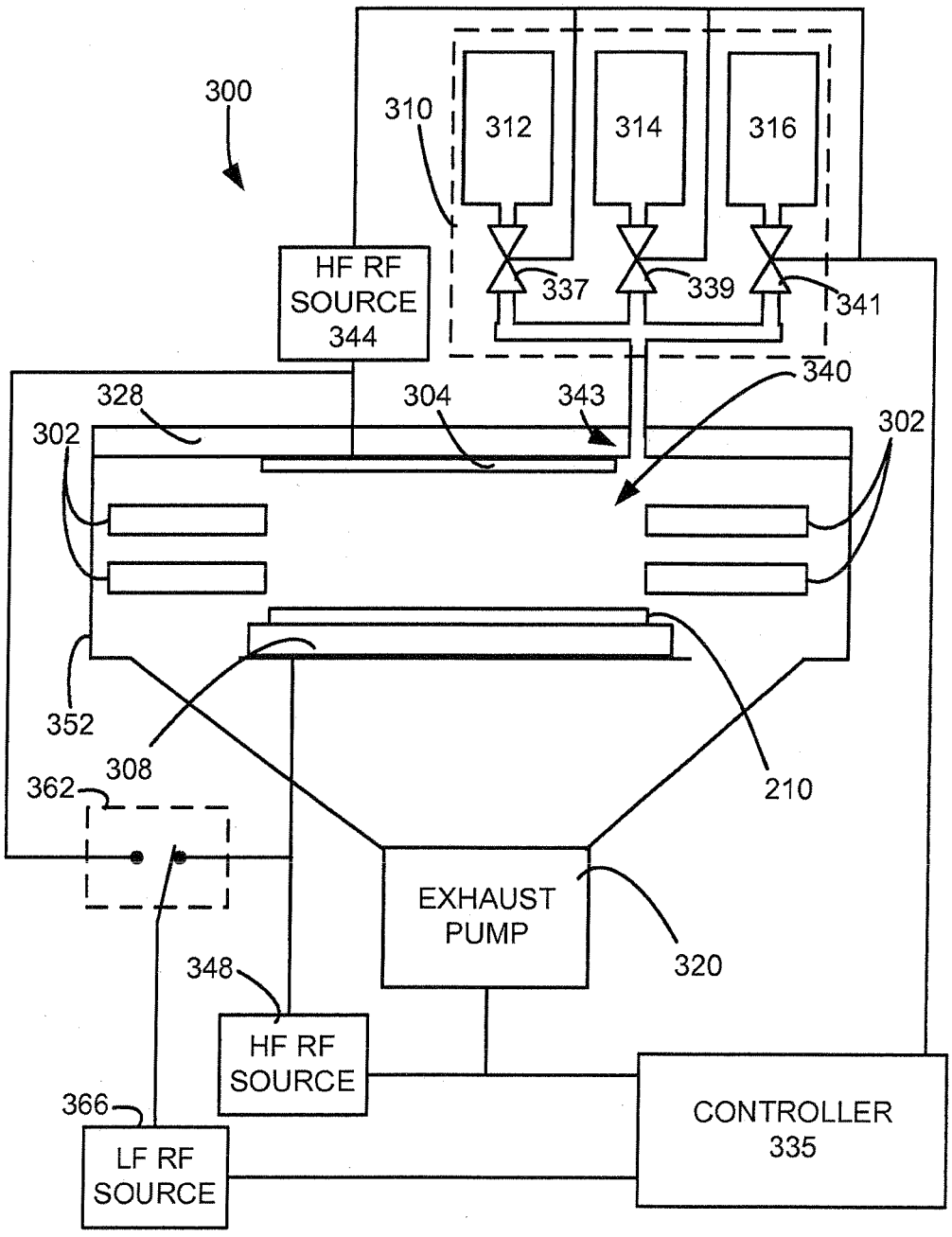

300
310
312
314
316
HF RF SOURCE 344
337
339
341
340
328
304
343
302
302
352
308
362
210
EXHAUST PUMP
320
348
HF RF SOURCE
366
LF RF SOURCE
CONTROLLER 335

FIG. 3

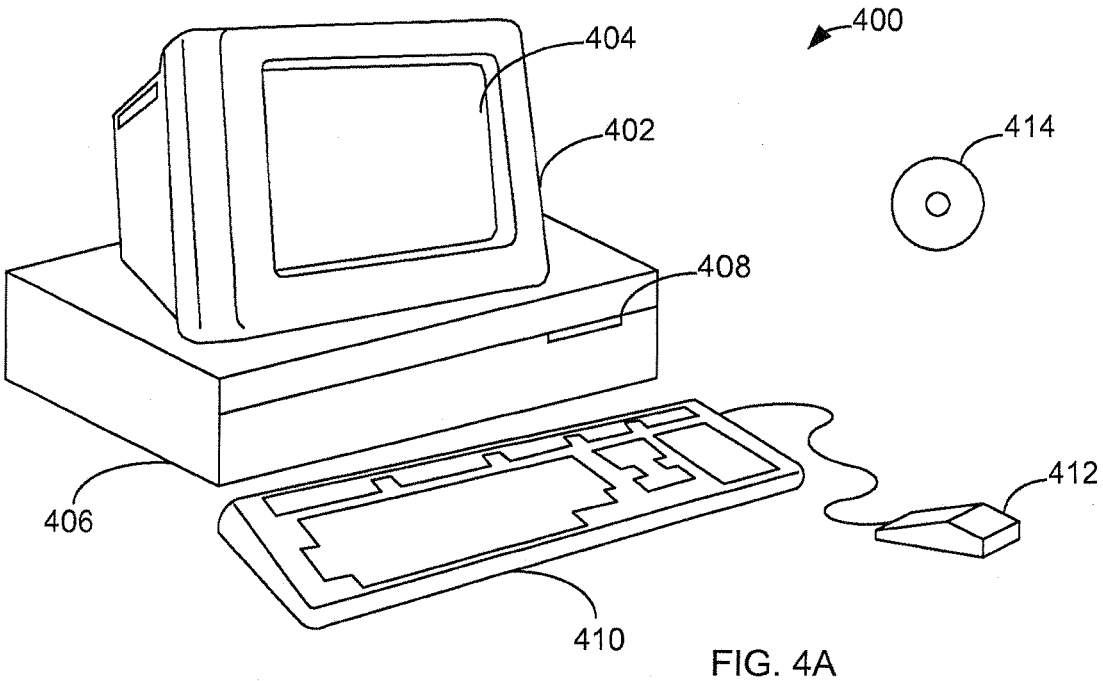

400
404
402
414
408
406
412
410

FIG. 4A

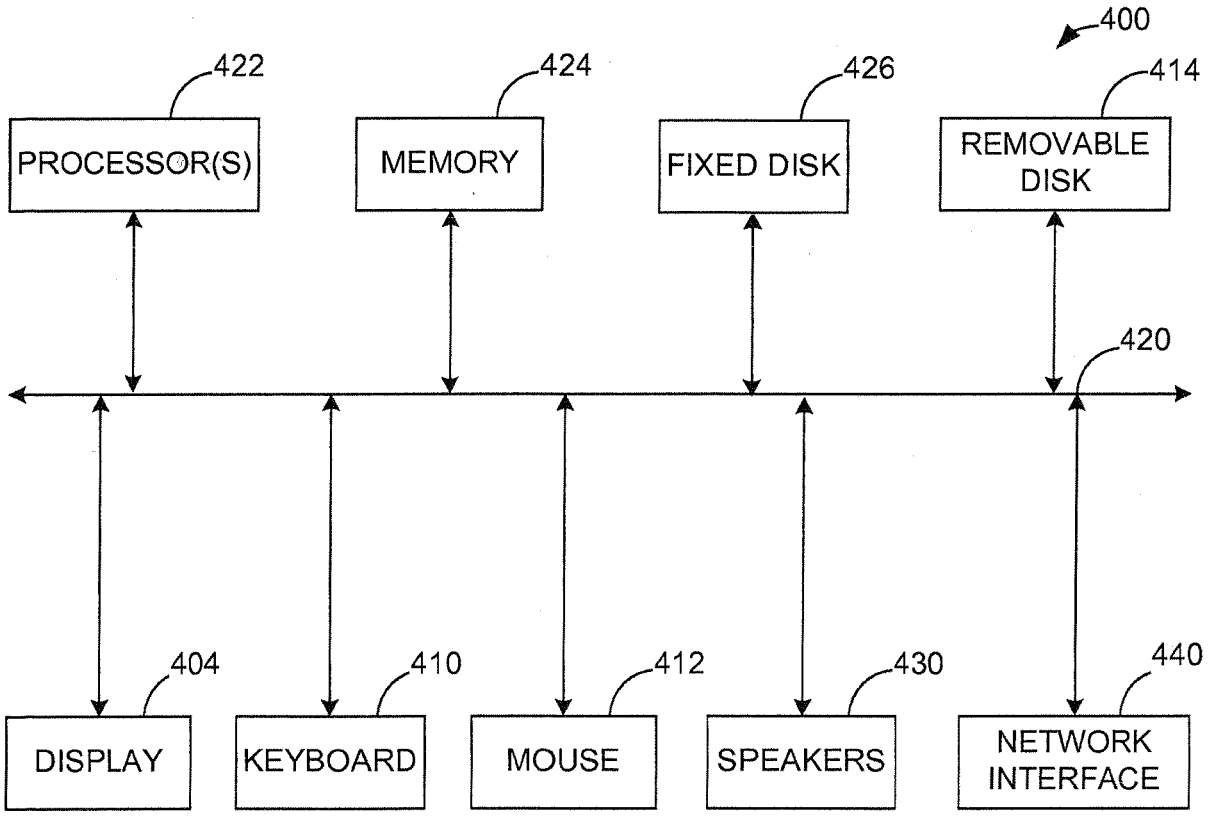

400
422
424
426
414
PROCESSOR(S)
MEMORY
FIXED DISK
REMOVABLE DISK
420
404
410
412
430
440
DISPLAY
KEYBOARD
MOUSE
SPEAKERS
NETWORK INTERFACE

FIG. 4B

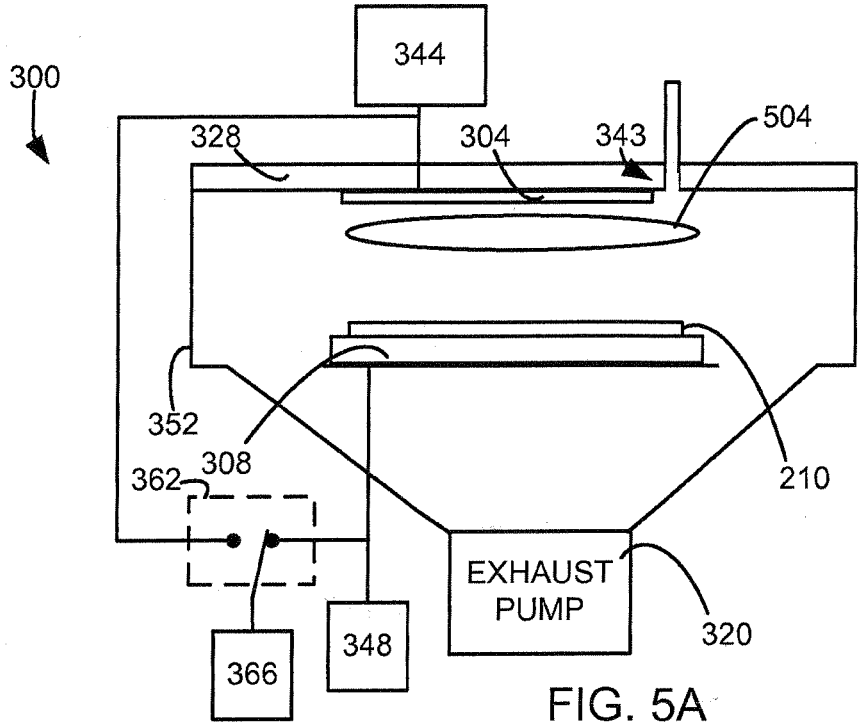

300
344
328
304
343
504
352
308
362
210
EXHAUST PUMP
320
348
366

FIG. 5A

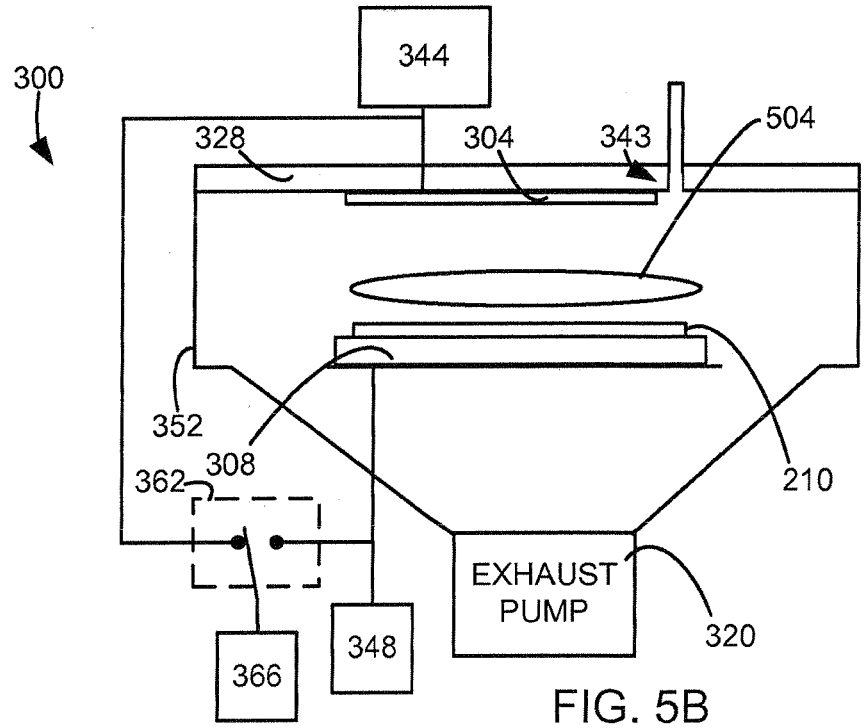

300
344
328
304
343
504
352
308
362
210
EXHAUST PUMP
320
348
366

FIG. 5B

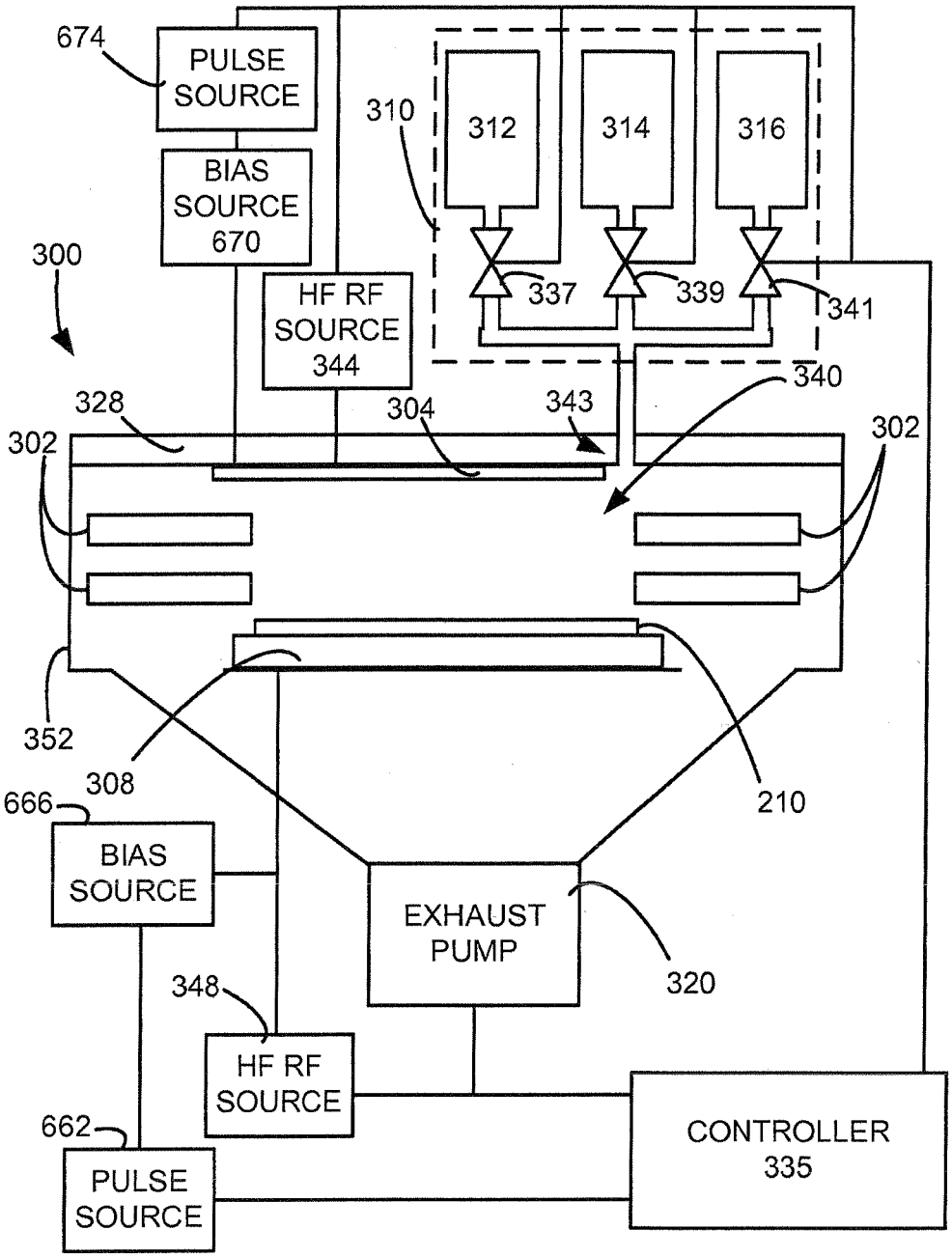

674
PULSE SOURCE
BIAS SOURCE 670
310
312
314
316
300
HF RF SOURCE 344
337
339
341
340
328
304
343
302
302
352
308
210
666
BIAS SOURCE
EXHAUST PUMP
320
348
HF RF SOURCE
662
PULSE SOURCE
CONTROLLER 335

FIG. 6